# VS-HFA16TB120S-M3

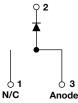
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# HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 16 A



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PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub>	16 A							
V <sub>R</sub>	1200 V							
V <sub>F</sub> at I <sub>F</sub>	2.3 V							
t <sub>rr</sub> (typ.)	30 ns							
T <sub>J</sub> max.	150 °C							
Package	D <sup>2</sup> PAK (TO-263AB)							
Circuit configuration	Single							

### FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

### DESCRIPTION

VS-HFA16TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>BBM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Cathode to anode voltage	V <sub>R</sub>		1200	V					
Maximum continuous forward current	١ <sub>F</sub>	T <sub>C</sub> = 100 °C	16						
Single pulse forward current	I <sub>FSM</sub>		190	А					
Maximum repetitive forward current	I <sub>FRM</sub>		64						
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	151	W					
Maximum power dissipation		T <sub>C</sub> = 100 °C	60	~~					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					

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ELECTRICAL SPECIFICATIONS (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-				
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 16 A		-	2.5	3.0	V		
		I <sub>F</sub> = 32 A	See fig. 1	-	3.2	3.93			
		I <sub>F</sub> = 16 A, T <sub>J</sub> = 125 °C		-	2.3	2.7			
Maximum reverse	1	$V_{R} = V_{R}$ rated	0	-	0.75	20			
leakage current	I <sub>RM</sub>	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	375	2000	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V See fig. 3		-	27	40	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH		

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5 and 10	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/μs, V <sub>R</sub> = 30 V	-	30	-	ns		
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	90	135			
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 16 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	164	245			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	5.8	10	A nC		
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	8.3	15			
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	260	675			
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	680	1838	nc		
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	120	-			
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	76	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	0.83	K/W			
Thermal resistance, junction-to-ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	r∨ vv			
Waight			-	2.0	-	g			
Weight			-	0.07	-	oz.			
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	HFA16TB120S						

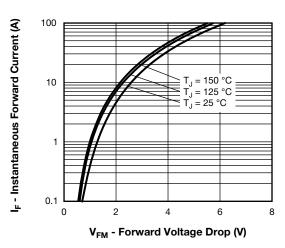
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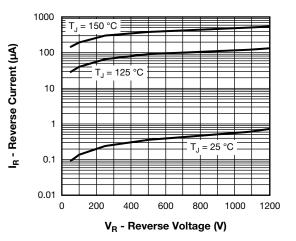
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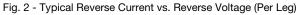


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Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)





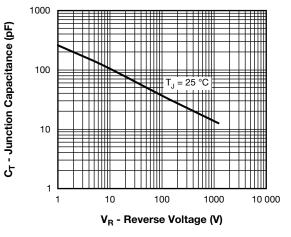


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

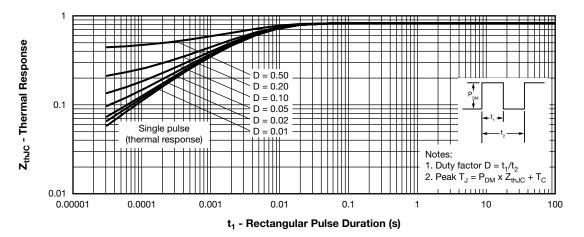


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Leg)

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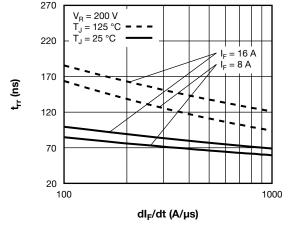


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Leg)

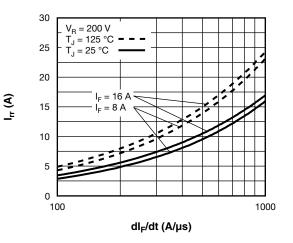


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt (Per Leg)

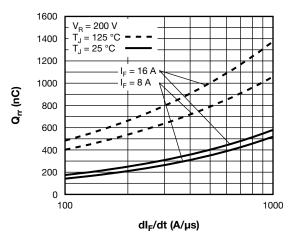


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt (Per Leg)

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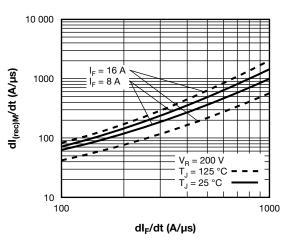
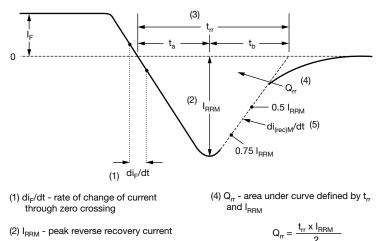


Fig. 8 - Typical dI<sub>(rec)M</sub>/dt vs. dI<sub>F</sub>/dt (Per Leg)



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(2) I<sub>RRM</sub> - peak reverse recovery current

(3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75  $I_{\text{RRM}}$  and 0.50  $I_{\text{RRM}}$  extrapolated to zero current.

(5) di<sub>(rec)M</sub>/dt - peak rate of change of

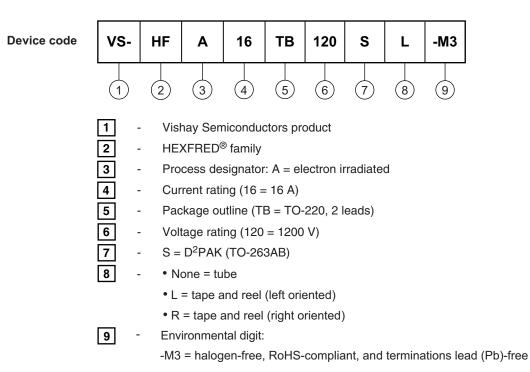
current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

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ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-HFA16TB120S-M3	50	Antistatic plastic tube							
VS-HFA16TB120SR-M3	800	13" diameter reel							
VS-HFA16TB120SL-M3	800	13" diameter reel							

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?96164						
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					

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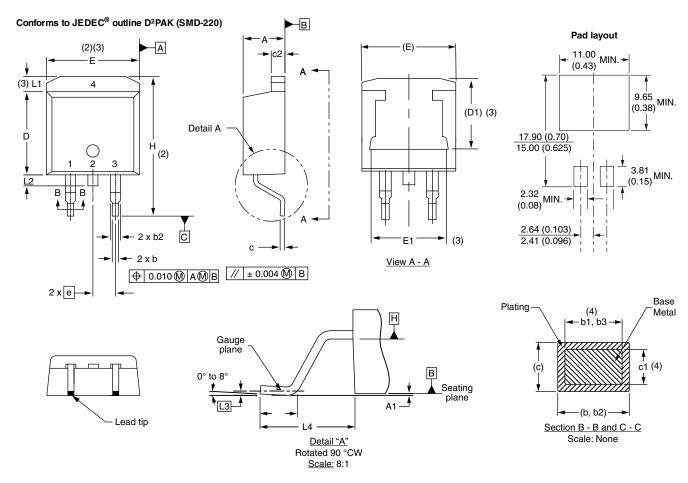


# **Outline Dimensions**

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D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	INCHES NOTES		NOTES SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	UIES	STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54 BSC 0.100 BSC		BSC		
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inches

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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